





ZXTD619MC

DUAL 50V NPN LOW SATURATION SWITCHING TRANSISTOR

Features and Benefits

- BVCEO > 50V
- I_C = 4A Continuous Collector Current
- Low Saturation Voltage (100mV max @ 1A)
- $R_{SAT} = 68m\Omega$ for Low Equivalent On Resistance
- hFE specified up to 6A for high current gain holds up
- Dual NPN saving footprint and component count •
- Low profile 0.8mm high package for thin applications •
- R_{0JA} efficient, 40% lower than SOT26 •
- 6mm² footprint, 50% smaller than TSOP6 and SOT26 •
- Lead-Free, RoHS Compliant (Note 1) .
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: DFN3020B-8
- Case Material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe.
- UL Flammability Rating 94V-0
- Nominal package height: 0.8mm
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.013 grams (approximate)

Applications

- DC DC Converters
- MOSFET gate drivers
- Charging circuits
- Motor Control
- Power switches
- Portable applications



Top View

Bottom View



C2



NPN Transistor

Bottom View Pin Out

Pin 1

Equivalent Circuit

Ordering Information (Note 3)

Product Marking Reel size (inches) Tape width (mm) Quant	
inditating iteration indition of the indition	ty per reel
ZXTD619MCTA DCC 7 8 3	3,000

Notes: 1. No purposefully added lead.

2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

3. For Packaging Details, go to our website at http://www.diodes.com.

Marking Information



DCC = Product type Marking Code Top view, dot denotes Pin 1



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Maximum Ratings @TA = 25°C unless otherwise specified

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	7	V
Peak Pulse Current	I _{CM}	6	А
Continuous Collector Current (Note 4 and 7)	Ic	4	A
Base Current	IB	1	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit	
	(Notes 4 & 7)		1.5 12		
Power Dissipation Linear Derating Factor	(Notes 5 & 7)		2.45 19.6	W	
	(Notes 6 & 7)	P _D	1.13 8	mW/°C	
	(Notes 6 & 8)		1.7 13.6		
Thermal Resistance, Junction to Ambient	(Notes 4 & 7)		83.3		
	(Notes 5 & 7)		51.0		
	(Notes 6 & 7)	R _{0JA}	111	°C/W	
	(Notes 6 & 8)		73.5		
Thermal Resistance, Junction to Lead (Notes 7 & 9)		R _{θJL}	17.1		
Operating and Storage Temperature Range	•	TJ, TSTG	-55 to +150	°C	

4. For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is Notes: 4. For a dual device surface mounted on 26 mm x 26 mm (corr) FR4 PCB with high coverage of single steed 2.02 copper, in stin air conditions, it measured when operating in a steady-state condition. The heatsn'th is split in half with the exposed collector pads connected to each half.
5. Same as note (4), except the device is measured at t <5 sec.
6. Same as note (4), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 102 copper.
7. For a dual device with 0 active die.
8. For dual device with 2 active die running at equal power.
9. The real value device for a state of the real state active.

9. Thermal resistance from junction to solder-point (at the end of the collector lead).





Thermal Characteristics



Power Dissipation v Board Area





Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V _{(BR)CBO}	100	190	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	V _{(BR)CEO}	50	65	-	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	7	8.2	-	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	-	-	100	nA	V _{CB} = 80V
Emitter Cutoff Current	I _{EBO}	-	-	100	_ nA	$V_{EB} = 6V$
Collector Emitter Cutoff Current	ICES	-	-	100	nA	$V_{CES} = 40V$
Static Forward Current Transfer Ratio (Note 10)	hfe	200 300 200 100 -	400 450 400 225 40	- - - -	- - - -	$\begin{split} I_{C} &= 10 \text{mA}, V_{CE} = 2 \text{V} \\ I_{C} &= 200 \text{mA}, V_{CE} = 2 \text{V} \\ I_{C} &= 1 \text{A}, V_{CE} = 2 \text{V} \\ I_{C} &= 2 \text{A}, V_{CE} = 2 \text{V} \\ I_{C} &= 6 \text{A}, V_{CE} = 2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}		10 70 145 115 225 270	20 100 200 220 300 320	mV mV mV mV mV	$\begin{split} &I_{C} = 0.1A, I_{B} = 10 \text{mA} \\ &I_{C} = 1A, I_{B} = 50 \text{mA} \\ &I_{C} = 1A, I_{B} = 10 \text{mA} \\ &I_{C} = 2A, I_{B} = 50 \text{mA} \\ &I_{C} = 3A, I_{B} = 100 \text{mA} \\ &I_{C} = 4A, I_{B} = 200 \text{mA} \end{split}$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	-	0.94	1.00	V	$I_{C} = 4A, V_{CE} = 2V$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	-	1.00	1.07	V	$I_{\rm C} = 4$ A, $I_{\rm B} = 200$ mA
Output Capacitance	C _{obo}	-	12	20	pF	V _{CB} = 10V. f = 1MHz
Transition Frequency	f _T	100	165	-	MHz	$V_{CE} = 10V, I_C = 50mA, f = 100MHz$
Turn-on Time	t _{on}	-	170	-	ns	$V_{CC} = 10V, I_{C} = 1A$
Turn-off Time	toff	-	750	-	ns	$I_{B1} = I_{B2} = 10 \text{mA}$

Notes: 10. Measured under pulsed conditions. Pulse width \leq 300 µs. Duty cycle \leq 2%





Typical Electrical Characteristics







Package Outline Dimensions



DFN3020B-8					
Dim	Min	Max	Тур		
Α	0.77	0.83	0.80		
A1	0	0.05	0.02		
A3	-	-	0.15		
b	0.25	0.35	0.30		
D	2.95	3.075	3.00		
D2	0.82	1.02	0.92		
D4	1.01	1.21	1.11		
е	-	-	0.65		
Е	1.95	2.075	2.00		
E2	0.43	0.63	0.53		
L	0.25	0.35	0.30		
Ζ	-	-	0.375		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
С	0.650
G	0.285
G1	0.090
Х	0.400
X1	1.120
Y	0.730
Y1	0.500
Y2	0.365



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